

## Zener Diode Chips (Dual Pad) for ESD Protection

### 1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge (ESD) protection application
- 1-2 This specification applies to P-Type silicon Zener diode chip (Dual pad) Device NO:WT-Z210P

### 2. Structure:

- 2-1 Planar type: Silicon Diode
- 2-2 Electrodes:
  - Top side:Aluminum Alloy(Anode).
  - Back side:Gold Layer(Cathode).

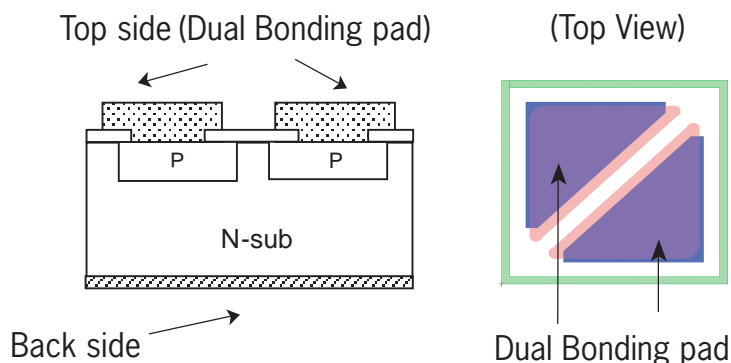
### 3. Size:

- 3-1 Chip size: 11.0 mils × 11.0 mils (280 um × 280 um).
- 3-2 Chip thickness: 6.0 ± 1.0 mils (152 ± 25.4 um).
- 3-3 Active area: 1/2 × 7.3 mils × 7.3 mils × 2 (1/2 × 186 um × 186 um × 2).
- 3-4 Dual Bonding pad: 1/2 × 6.8 mils × 6.8 mils × 2 (1/2 × 173 um × 173 um × 2).  
Hight of Hypotenuse: 5.23 mils(133 um).
- 3-5 Pattern drawing: Refer to the attached drawing.

### 4. Electrical Characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	Vz	Iz=5mA	5.8	6.3	6.8	V
Forward Voltage	Vf	If=20mA			1.2	v
Reverse Leakage Current	IR	VR=4V VR=5V			100 500	nA
Electrostatic Discharge	ESD	HBM MIL-STD 883	8.0			KV

### 5. Drawing:



### 6. Protection Circuit:

